

| | L # | Hits | Search Text | DBs | Time Stamp |
|---|-----|-------|---|--|---------------------|
| 1 | L1 | 4112 | MRAM or (magnetoresist\$6 adj semiconductor adj memory) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 2 | L2 | 71310 | read/write | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 3 | L3 | 1293 | read/write near4 current | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 4 | L4 | 5526 | write adj current | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |

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|---|-----|-------|---|--|---------------------|
| 5 | L5 | 746 | (MRAM or (magnetoresist\$6 adj semiconductor adj memory)) and (write adj current) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 6 | L6 | 4788 | MRAM or (magnetoresist\$6 near4 memory) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 7 | L7 | 98 | (MRAM or (magnetoresist\$6 near4 memory)) and (read/write near4 current) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 8 | L8 | 52942 | (multilevel or multi-level or third or fourth) near2 line | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |

| | L # | Hits | Search Text | DBs | Time Stamp |
|----|-----|-------|---|--|---------------------|
| 9 | L9 | 23811 | selection near2 line | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 10 | L10 | 399 | (MRAM or (magnetoresist\$6 near4 memory)) and ((multilevel or multi-level or third or fourth) near2 line) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 11 | L15 | 4807 | MRAM or (magnetoresist\$6 adj random adj access adj memory) or (magnetoresist\$6 near2 RAM) or (magnetoresist\$6 near4 memory) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 12 | L16 | 787 | L15 and L4 | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |

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|----|-----|--------|-----------------------------------|--|---------------------|
| 13 | L18 | 2254 | (438/622) .CCLS. | US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 14 | L22 | 855 | three adj dimensional adj circuit | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 15 | L26 | 272768 | three adj dimensional | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 16 | L28 | 696 | magnetic adj ram | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |

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|----|-----|------|--|---|---------------------|
| 17 | L11 | 92 | (MRAM or (magnetoresist\$6 adj semiconductor adj memory)) and (read/write near4 current) | US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD_B | 2004/12/29 18:07 |
| 18 | L19 | 8 | L18 and L15 | US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD_B | 2004/12/29 18:07 |
| 19 | L20 | 3 | L14 and L15 | US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD_B | 2004/12/29 18:07 |
| 20 | L21 | 2 | ("6211559").PN. | US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TD_B | 2004/12/29 18:07 |

| | L # | Hits | Search Text | DBs | Time Stamp |
|----|-----|------|---|--|---------------------|
| 21 | L23 | 3 | L22 and L9 | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 22 | L29 | 27 | L28 and L9 | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 23 | L13 | 117 | ((MRAM or (magnetoresist\$6 near4 memory)) and ((multilevel or multi-level or third or fourth) near2 line)) and (selection near2 line) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 24 | L17 | 147 | L16 and L9 | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |

| | L # | Hits | Search Text | DBs | Time Stamp |
|----|-----|------|---|--|---------------------|
| 25 | L14 | 242 | (438/620) .CCLS. | US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 26 | L25 | 218 | L22 and (memory or ROM) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 27 | L27 | 249 | L26 and MRAM | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |
| 28 | L12 | 786 | (MRAM or (magnetoresist\$6 near4 memory)) and (write adj current) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:07 |

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| 29 | L24 | 855 | three adj dimensional adj circuit | US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B | 2004/12/29 18:07 |
| 30 | L30 | 210 | (365/157) .CCLS. | US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B | 2004/12/29 18:24 |
| 31 | L31 | 909 | (365/158) .CCLS. | US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B | 2004/12/29 18:24 |
| 32 | L32 | 239 | (365/130) .CCLS. | US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B | 2004/12/29 18:25 |

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|----|-----|------|----------------------|--|---------------------|
| 33 | L33 | 191 | (365/148).CCLS. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:25 |
| 34 | L34 | 1502 | 30 or 31 or 32 or 33 | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:26 |
| 35 | L35 | 29 | 34 and 438/? .ccls. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:38 |
| 36 | L36 | 1483 | (438/3).CCLS. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:38 |

| | L # | Hits | Search Text | DBs | Time Stamp |
|----|-----|------|------------------|--|---------------------|
| 37 | L37 | 675 | (438/48) .CCLS. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:39 |
| 38 | L38 | 39 | (438/171) .CCLS. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 18:39 |
| 39 | L39 | 291 | (438/210) .CCLS. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2004/12/29 19:53 |